



Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 500 A



PRIMARY CHARACTERISTICS				
I _{T(AV)} 500 A				
V _{DRM} /V _{RRM}	400 V, 600 V			
V_{TM}	1.36 V			
I _{GT}	90 mA			
TJ	-40 °C to +125 °C			
Package	A-PUK (TO-200AB)			

Single SCR

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB))
- Designed and qualified for industrial level
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		500	А		
$I_{T(AV)}$	T _{hs}	55	°C		
I _{T(RMS)}		960	А		
	T _{hs}	25	°C		
I _{TSM}	50 Hz	7850	Α		
	60 Hz	8220			
l ² t	50 Hz	308	kA ² s		
	60 Hz	281			
V _{DRM} /V _{RRM}		400 to 600	V		
tq	Typical	100	μs		
T _J		- 40 to 125	°C		

ELECTRICAL SPECIFICATIONS

Circuit configuration

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{split} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J &= T_J & \text{MAXIMUM} \\ & \text{mA} \end{split}$				
ST280CC	04	400	500	30				
3120000	06	600	700	30				



VS-ST280C

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PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	1	180° conduction, half sine wave		500 (185)	Α	
at heatsink temperature	I _{T(AV)}	double side	(single side) cod	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C heatsink temperature double side cooled			960	
		t = 10 ms	No voltage		7850	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		8220	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial T _J = T _J maximum	6600	
		t = 8.3 ms	reapplied		6900	
	l ² t	t = 10 ms	No voltage		308	
Maximum I ² t for fusing		t = 8.3 ms	reapplied		281	
		t = 10 ms	100 % V _{RRM}		218	
		t = 8.3 ms	reapplied		200	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			3080	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.84	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r _{t1}	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.50	~ 0
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.47	mΩ
Maximum on-state voltage	V_{TM}	$I_{pk} = 1050 \text{ A}, T_J = 125 \text{ °C}, t_p = 10 \text{ ms sine pulse}$			1.36	V
Maximum holding current	I _H	T 05 00		0.1/	600	^
Maximum (typical) latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load			1000 (300)	0) mA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	tq	I_{TM} = 300 A, T_J = T_J maximum, dI/dt = 20 A/ μ s, V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 100 Ω , t_p = 500 μ s	100	μs		

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



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TRIGGERING								
DADAMETER	CVMPOL		CT CONDITIONS	VALUES				
PARAMETER	SYMBOL		TEST CONDITIONS -		MAX.	UNITS		
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10	0.0	W		
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV		
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3	.0	Α		
Maximum peak positive gate voltage	+ V _{GM}	+ V _{GM}		T. T. marriage at 2.5 marriage		20		V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms 5.0		.0	V			
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA		
		T _J = 25 °C		90	150			
		T _J = 125 °C		40	-			
		T _J = - 40 °C		2.9	-			
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		1.8	3.0	٧		
		T _J = 125 °C		1.2	-			
DC gate current not to trigger	I _{GD}	T T manyimay ma	Maximum gate current/voltage not to trigger is the maximum	1	0	mA		
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.30		V		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		- 40 to 125	°C		
Maximum storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation single side cooled	0.17			
		DC operation double side cooled	0.08	K/W		
Maximum thermal resistance,	0	DC operation single side cooled	0.033	IV VV		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.017			
Mounting force, ± 10 %			4900 (500)	N (kg)		
Approximate weight			50	g		
Case style		See dimensions - link at the end of datasheet	A-PUK (TO-200	AB)		

△R _{thJC} CONDUCTION								
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR	CONDUCTION	TEST CONDITIONS	LIMITO		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.016	0.016	0.011	0.011	$T_J = T_J$ maximum			
120°	0.019	0.019	0.019	0.019		K/W		
90°	0.024	0.024	0.026	0.026				
60°	0.035	0.035	0.036	0.037				
30°	0.060	0.060	0.060	0.061				

Note

[•] The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC



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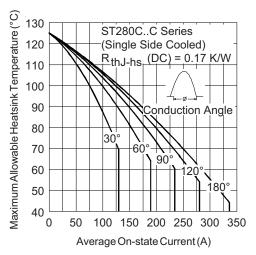


Fig. 1 - Current Ratings Characteristics

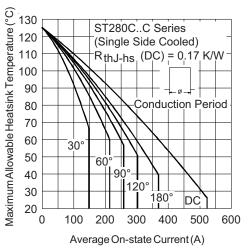


Fig. 2 - Current Ratings Characteristics

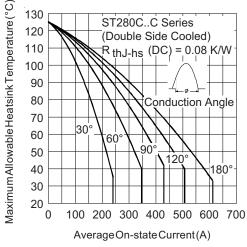


Fig. 3 - Current Ratings Characteristics

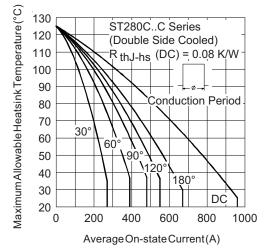


Fig. 4 - Current Ratings Characteristics

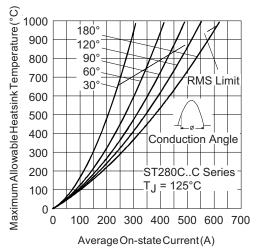


Fig. 5 - On-State Power Loss Characteristics

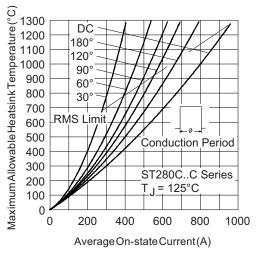


Fig. 6 - On-State Power Loss Characteristics



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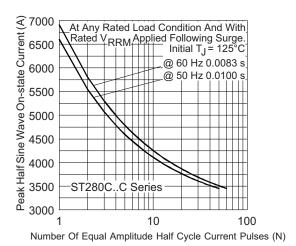


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

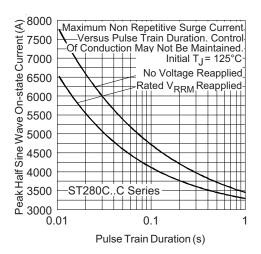


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

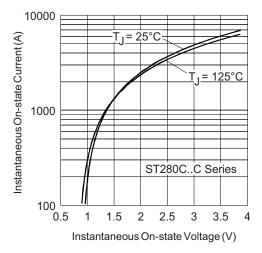


Fig. 9 - On-State Voltage Drop Characteristics

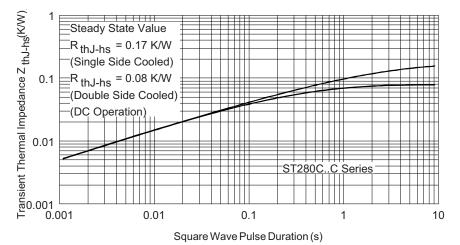


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics



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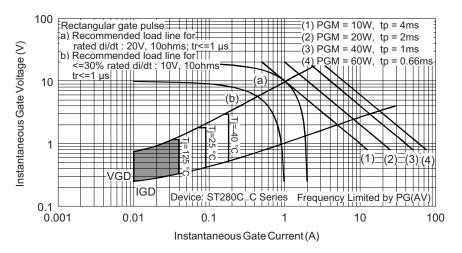
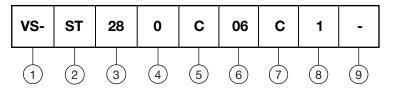


Fig. 11 - Gate Charactersitics

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Thyristor

Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code: code x 100 = V_{RRM} (see Voltage Ratings table)

7 - C = PUK case A-PUK (TO-200AB)

0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95074			

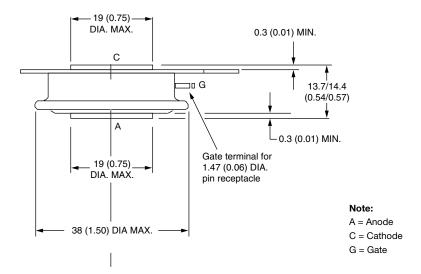


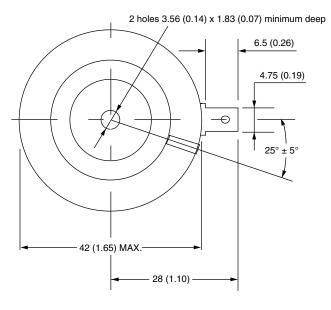
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A-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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